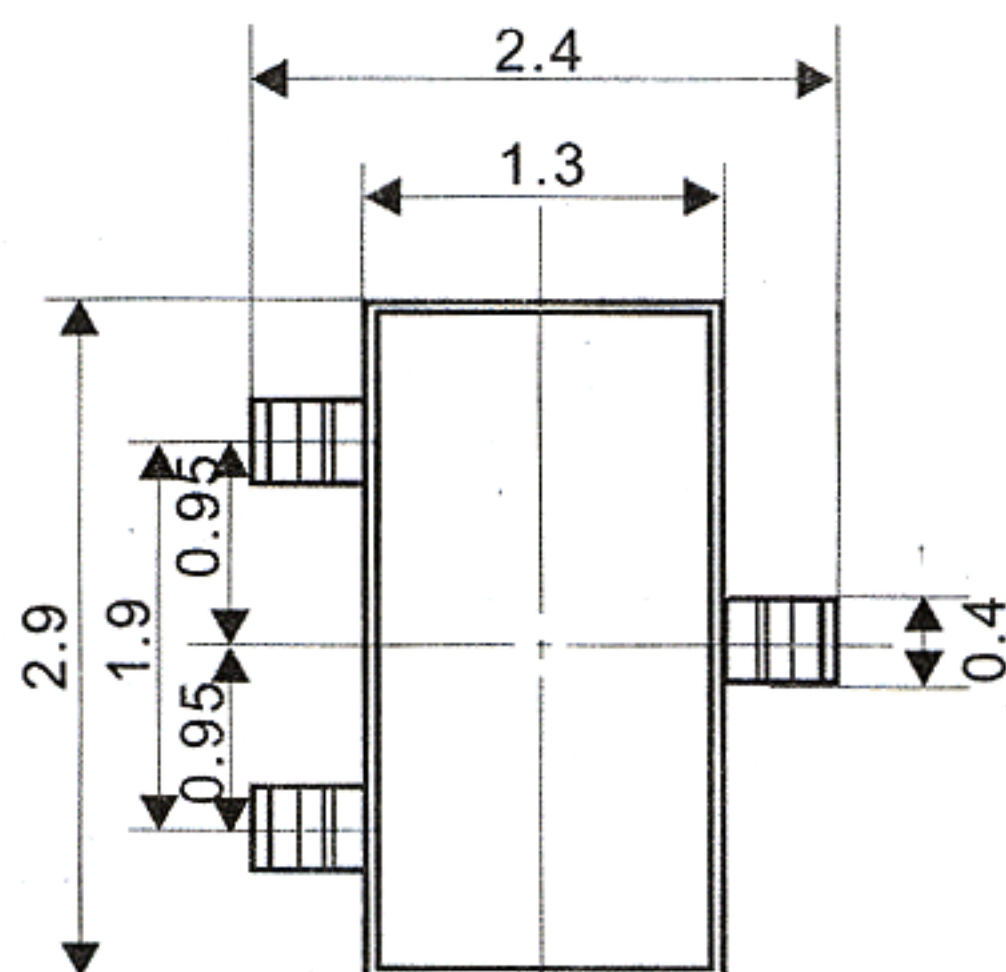
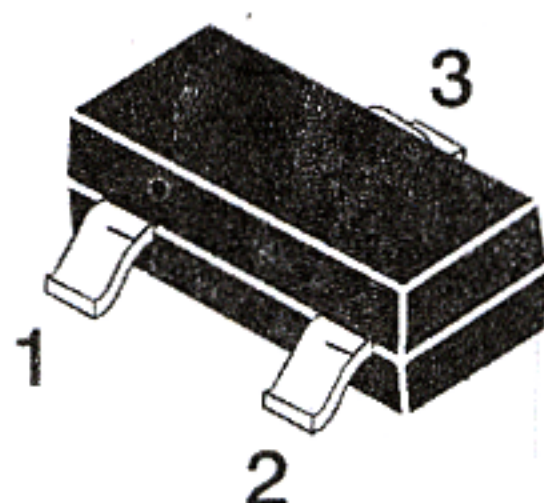
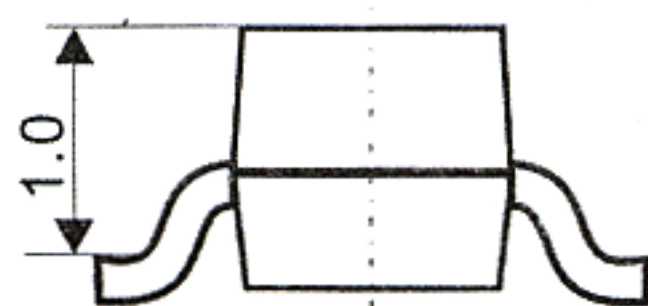


SOT-23 Plastic-Encapsulate Transistors

KTC3875 TRANSISTOR (NPN)

- 1.BASE
- 2.EMITTER
- 3.COLLECTOR



UNIT: mm

FEATURES

Power dissipation

P_{CM} : 0.15 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.15 A

Collector-base voltage

$V_{(BR)CBO}$: 60V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amp}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Drain-source Breakdown Voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	60		V
Collector Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	50		
Emitter-base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5		
Collector Cut-off Current	I_{CBO}	$V_{CB}=60V, I_E=0$		0.1	μA
Collector Cut-off Current	I_{CEO}	$V_{CE}=45V, I_B=0$		0.2	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$		0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=6V, I_C=2mA$	70	700	
Collector-emitter Saturation Voltage	V_{CEsat}	$I_C=100mA, I_B=10mA$		0.25	V
Base-emitter Saturation Voltage	V_{BEsat}	$I_C=100mA, I_B=10mA$		1	V
Transition Frequency	f_T	$V_{CE}=10V, I_C=1mA$	80		MHz

CLASSIFICATION OF h_{FE}

RANK	O	Y	GR	BL
RANGE	70-140	120-240	200-400	350-700
DEVICE MARKING	ALO	ALY	ALG	ALL